IN THE CLAIMS:

1. (Withdrawn) A method of manufacturing a semiconductor device, said method comprising the steps of:

crystallizing an amorphous semiconductor film by irradiating with a laser light to form a crystalline semiconductor film having a warp;

heating the crystalline semiconductor film to lessen the warp;

etching the crystalline semiconductor film after the heating step to form a crystalline semiconductor island.

2. (Withdrawn) A method of manufacturing a semiconductor device, said method comprising the steps of:

crystallizing an amorphous semiconductor film by irradiating with a laser light to form a crystalline semiconductor film having a warp;

etching the crystalline semiconductor film to form a crystalline semiconductor island;

heating the crystalline semiconductor island to lessen the warp.

3. (Withdrawn) A method of manufacturing a semiconductor device, said method comprising the steps of:

crystallizing an amorphous semiconductor film by irradiating with a laser light to form a crystalline semiconductor film having a warp;

heating the crystalline semiconductor film at a temperature in a range of 500°C or higher to lessen the warp.

4. (Withdrawn) A method according to claim 1,

wherein the crystalline semiconductor film is heated at a temperature in a range of 500°C or higher.

5. (Withdrawn) A method according to claim 2,

wherein the crystalline semiconductor island is heated at a temperature in a range of 500°C or higher.

6. (Currently Amended) A method of manufacturing a semiconductor device, ~~said~~ the method comprising the steps of:

adding a metal element to an amorphous semiconductor film;

first heating the amorphous semiconductor film to form a first crystalline semiconductor film;

irradiating the first crystalline semiconductor film with a laser light to form a second crystalline semiconductor film having a warp;

second heating the second crystalline semiconductor film at a higher temperature than the first heating step to lessen the warp.

7. (Currently Amended) A method of manufacturing a semiconductor device, ~~said~~ the method comprising the steps of:

adding a metal element to an amorphous semiconductor film;

first heating the amorphous semiconductor film to form a first crystalline semiconductor film;

irradiating the first crystalline semiconductor film with a laser light to form a second crystalline semiconductor film having a warp;

second heating the second crystalline semiconductor film at a higher temperature than the first heating step to lessen the warp;

etching the second crystalline semiconductor film after the second heating step to form a crystalline semiconductor island.

8. (Currently Amended) A method of manufacturing a semiconductor device, ~~said~~ the method comprising the steps of:

adding a metal element to an amorphous semiconductor film;

first heating the amorphous semiconductor film to form a first crystalline semiconductor film;

irradiating the first crystalline semiconductor film with a laser light to form a second crystalline semiconductor film having a warp;

etching the second crystalline semiconductor film to form a crystalline semiconductor island;

second heating the crystalline semiconductor island at a higher temperature than the first heating step to lessen the warp.

9. (Withdrawn) A method according to claim 1,

wherein the laser light is one selected from the group consisting of a pulse oscillation type exciter laser, a pulse oscillation type YAG laser, a pulse oscillation type YVO_4 laser, a pulse oscillation type $YA1O_3$ laser, a pulse oscillation type YLF laser, a continuous emission type excimer laser, a continuous emission type YAG laser, a continuous emission type YVO_4 laser, a continuous emission type $YA1O_3$ laser, and a continuous emission type YLF laser.

10. (Withdrawn) A method according to claim 1,

wherein the laser light has at least one selected from the group consisting of a rectangular shape and a linear shape on an irradiation plane.

11. (Withdrawn) A method according to claim 1,

wherein an annealing furnace is used in the heating step.

12. (Withdrawn) A method according to claim 1,

wherein a lamp light is radiated in the heating step.

13. (Withdrawn) A method according to claim 1,

wherein the crystalline semiconductor film is heated for 1-30 minutes in the heating step.

14. (Withdrawn) A method according to claim 12,

wherein the lamp light is radiated from at least one selected from the group consisting of an upper side and a lower side of a substrate.

15. (Withdrawn) A method according to claim 12,

wherein the lamp light is radiated from at least one selected from the group consisting of a halogen lamp, a metal halide lamp, a xenon arc lamp, a carbon arc lamp, a high pressure sodium lamp, and a high pressure mercury lamp.

16. (Withdrawn) A method according to claim 12,

wherein the lamp light is radiated with a temperature rising rate or a temperature lowering rate of 30 to 300°C per minute.

17. (Currently Amended) ~~A~~ The method according to claim 6,

wherein an annealing furnace is used in the second heating step.

18. (Currently Amended) ~~A~~ The method according to claim 6,

wherein a lamp light is radiated in the second heating step.

19. (Currently Amended) ~~A~~ The method according to claim 6,

wherein the second crystalline semiconductor film is heated for 1-30 minutes in the second heating step.

20. (Currently Amended) ~~A~~ The method according to claim 18,

wherein the lamp light is radiated from at least one ~~selected from the group consisting~~ of an upper side and a lower side of a substrate.

21. (Currently Amended) ~~A~~ The method according to claim 18,

wherein the lamp light is radiated from at least one selected from the group consisting of a halogen lamp, a metal halide lamp, a xenon arc lamp, a carbon arc lamp, a high pressure sodium lamp, and a high pressure mercury lamp.

22. (Currently Amended) ~~A~~ The method according to claim 18,

wherein the lamp light is radiated with a temperature rising rate or a temperature lowering rate of 30 to 300°C per minute.

23. (Withdrawn) A method according to claim 1,

wherein the amorphous semiconductor film is formed through at least one selected from the group consisting of a sputtering method and an LPCVD method.

24. (Withdrawn) A method according to claim 1,

wherein the amorphous semiconductor film is formed through a plasma CVD method at a temperature in a range of 400°C or higher.

25. (Currently Amended) ~~A~~ The method according to claim 6,

wherein the metal element comprises at least one selected from the group consisting of Fe, Co, Ni, Ru, Rh, Pd, Os, Ir, Pt, Cu, Ag, Au, Sn and Sb.

26. (Withdrawn) A method according to claim 1,

wherein the semiconductor device is one selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle type display, a player using a recording medium, a digital camera, a front type projector, a rear type projector, a mobile telephone, a mobile book, and a display.

27. (Withdrawn) A method according to claim 2,

wherein the laser light is one selected from the group consisting of a pulse oscillation type excimer laser, a pulse oscillation type YAG laser, a pulse oscillation type $YV10_4$ laser, a pulse oscillation type $YA1O_3$ laser, a pulse oscillation type YLF laser, a continuous emission type excimer laser, a continuous emission type YAG laser; a continuous emission type YVO_4 laser, a continuous emission type $YA1O_3$ laser, and a continuous emission type YLF laser.

28. (Withdrawn) A method according to claim 2,

wherein the laser light has at least one selected from the group consisting of a rectangular shape and a linear shape on an irradiation plane.

29. (Withdrawn) A method according to claim 2,

wherein an annealing furnace is used in the heating step.

30. (Withdrawn) A method according to claim 2,

wherein a lamp light is radiated in the heating step.

31. (Withdrawn) A method according to claim 2,

wherein the crystalline semiconductor island is heated for 1-30 minutes in the heating step.

32. (Withdrawn) A method according to claim 30,

wherein the lamp light is radiated from at least one selected from the group consisting of an upper side and a lower side of a substrate.

33. (Withdrawn) A method according to claim 30,

wherein the lamp light is radiated from at least one selected from the group consisting of a halogen lamp, a metal halide lamp, a xenon arc lamp, a carbon arc lamp, a high pressure sodium lamp, and a high pressure mercury lamp.

34. (Withdrawn) A method according to claim 30,

wherein the lamp light is radiated with a temperature rising rate or a temperature lowering rate of 30 to 300°C per minute.

35. (Withdrawn) A method according to claim 2,

wherein the amorphous semiconductor film is formed through at least one selected from the group consisting of a sputtering method and an LPCVD method.

36. (Withdrawn) A method according to claim 2,

wherein the amorphous semiconductor film is formed through a plasma CVD method at a temperature in a range of 400°C or higher.

37. (Withdrawn) A method according to claim 2,

wherein the semiconductor device is one selected from the group consisting of a personal computer, a video camera, a mobile computer, a gaggle type display, a player using a recording medium, a digital camera, a front type projector, a rear type projector, a mobile telephone, a mobile book, and a display.

38. (Withdrawn) A method according to claim 3,

wherein the laser light is one selected from the group consisting of a pulse oscillation type excimer laser, a pulse oscillation type YAG laser, a pulse oscillation type YVO_4 laser, a pulse oscillation type $YA1O_3$ laser, a pulse oscillation type YLF laser, a continuous emission type excimer laser, a continuous emission type YAG laser, a continuous emission type YVO_4 laser, a continuous emission type $YA1O_3$ laser, and a continuous emission type YLF laser.

39. (Withdrawn) A method according to claim 3,

wherein the laser light has at least one selected from the group consisting of a rectangular shape and a linear shape on an irradiation plane.

40. (Withdrawn) A method according to claim 3,

wherein an annealing furnace is used in the heating step.

41. (Withdrawn) A method according to claim 3,

wherein a lamp light is radiated in the heating step.

42. (Withdrawn) A method according to claim 3,

wherein the crystalline semiconductor film is heated for 1-30 minutes in the heating step.

43. (Withdrawn) A method according to claim 41,

wherein the lamp light is radiated from at least one selected from the group consisting of an upper side and a lower side of a substrate.

44. (Withdrawn) A method according to claim 41,

wherein the lamp light is radiated from at least one selected from the group consisting of a halogen lamp, a metal halide lamp, a xenon arc lamp, a carbon arc lamp, a high pressure sodium lamp, and a high pressure mercury lamp.

45. (Withdrawn) A method according to claim 41,

wherein the lamp light is radiated with a temperature rising rate or a temperature lowering rate of 30 to 300°C per minute.

46. (Withdrawn) A method according to claim 3,

wherein the amorphous semiconductor film is formed through at least one selected from the group consisting of a sputtering method and an LPCVD method.

47. (Withdrawn) A method according to claim 3,

wherein the amorphous semiconductor film is formed through a plasma CVD method at a temperature in a range of 400°C or higher.

48. (Withdrawn) A method according to claim 3,

wherein the semiconductor device is one selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle type display, a player using a recording medium, a digital camera, a front type projector, a rear type projector, a mobile telephone, a mobile book, and a display.

49. (Currently Amended) ~~A~~ The method according to claim 6,

wherein the laser light is radiated from one selected from the group consisting of a pulse oscillation type excimer laser, a pulse oscillation type YAG laser, a pulse oscillation type YVO4 laser, a pulse oscillation type YAlO3 laser, a pulse oscillation type YLF laser, a continuous emission type excimer laser, a continuous emission type YAG laser, a continuous emission type YVO4 laser, a continuous emission type YAlO3 laser, and a continuous emission type YLF laser.

50. (Currently Amended) ~~A~~ The method according to claim 6,

wherein the laser light has ~~at least~~ one ~~selected from the group consisting~~ of a rectangular shape and a linear shape on an irradiation plane.

51. (Currently Amended) ~~A~~ The method according to claim 6,

wherein the amorphous semiconductor film is formed through ~~at least~~ one ~~selected from the group consisting~~ of a sputtering method and an LPCVD method.

52. (Currently Amended) ~~A~~ The method according to claim 6,

wherein the amorphous semiconductor film is formed through a plasma CVD method at a temperature in a range of 400°C or higher.

53. (Currently Amended) ~~A~~ The method according to claim 6,

wherein the semiconductor device is one selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle type display, a player using a recording medium, a digital camera, a front type projector, a rear type projector, a mobile telephone, a mobile book, and a display.

54. (Currently Amended) ~~A~~ The method according to claim 7,

wherein the laser light is radiated from one selected from the group consisting of a pulse oscillation type excimer laser, a pulse oscillation type YAG laser, a pulse oscillation type YVO4 laser, a pulse oscillation type YAlO3 laser, a pulse oscillation type YLF laser, a continuous emission type excimer laser, a continuous emission type YAG laser, a continuous emission type YVO4 laser, a continuous emission type YAlO3 laser, and a continuous emission type YLF laser.

55. (Currently Amended) ~~A~~ The method according to claim 7,

wherein the laser light has ~~at least~~ one ~~selected from the group consisting~~ of a rectangular shape and a linear shape on an irradiation plane.

56. (Currently Amended) ~~A~~ The method according to claim 7,

wherein an annealing furnace is used in the second heating step.

57. (Currently Amended) ~~A~~ The method according to claim 7, wherein a lamp light is radiated in the second heating step.

58. (Currently Amended) ~~A~~ The method according to claim 7, wherein the second crystalline semiconductor film is heated for 1-30 minutes in the second heating step.

59. (Currently Amended) ~~A~~ The method according to claim 57, wherein the lamp light is radiated from at least one ~~selected from the group consisting~~ of an upper side and a lower side of a substrate.

60. (Currently Amended) ~~A~~ The method according to claim 57, wherein the lamp light is radiated from at least one selected from the group consisting of a halogen lamp, a metal halide lamp, a xenon arc lamp, a carbon arc lamp, a high pressure sodium lamp, and a high pressure mercury lamp.

61. (Currently Amended) ~~A~~ The method according to claim 57, wherein the lamp light is radiated with a temperature rising rate or a temperature lowering rate of 30 to 300°C per minute.

62. (Currently Amended) ~~A~~ The method according to claim 7, wherein the amorphous semiconductor film is formed through ~~at least~~ one ~~selected from the group consisting~~ of a sputtering method and an LPCVD method.

63. (Currently Amended) ~~A~~ The method according to claim 7, wherein the amorphous semiconductor film is formed through a plasma CVD method at a temperature in a range of 400°C or higher.

64. (Currently Amended) ~~A~~ The method according to claim 7,

wherein the metal element comprises at least one selected from the group consisting of Fe, Co, Ni, Ru, Rh, Pd, Os, Ir, Pt, Cu, Ag, Au, Sn and Sb.

65. (Currently Amended) ~~A~~ The method according to claim 7,

wherein the semiconductor device is one selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle type display, a player using a recording medium, a digital camera, a front type projector, a rear type projector, a mobile telephone, a mobile book, and a display.

66. (Currently Amended) ~~A~~ The method according to claim 8,

wherein the laser light is radiated from one selected from the group consisting of a pulse oscillation type excimer laser, a pulse oscillation type YAG laser, a pulse oscillation type YVO4 laser, a pulse oscillation type YAlO3 laser, a pulse oscillation type YLF laser, a continuous emission type excimer laser, a continuous emission type YAG laser, a continuous emission type YVO4 laser, a continuous emission type YAlO3 laser, and a continuous emission type YLF laser.

67. (Currently Amended) ~~A~~ The method according to claim 8,

wherein the laser light has ~~at least~~ one ~~selected from the group consisting~~ of a rectangular shape and a linear shape on an irradiation plane.

68. (Currently Amended) ~~A~~ The method according to claim 8,

wherein an annealing furnace is used in the second heating step.

69. (Currently Amended) ~~A~~ The method according to claim 8,

wherein a lamp light is radiated in the second heating step.

70. (Currently Amended) ~~A~~ The method according to claim 8,

wherein the crystalline semiconductor island is heated for 1-30 minutes in the second heating step.

71. (Currently Amended) ~~A~~ The method according to claim 69,

wherein the lamp light is radiated from at least one ~~selected from the group consisting~~ of an upper side and a lower side of a substrate.

72. (Currently Amended) ~~A~~ The method according to claim 69,

wherein the lamp light is radiated from at least one selected from the group consisting of a halogen lamp, a metal halide lamp, a xenon arc lamp, a carbon arc lamp, a high pressure sodium lamp, and a high pressure mercury lamp.

73. (Currently Amended) ~~A~~ The method according to claim 69,

wherein the lamp light is radiated with a temperature rising rate or a temperature lowering rate of 30 to 300°C per minute.

74. (Currently Amended) ~~A~~ The method according to claim 8,

wherein the amorphous semiconductor film is formed through ~~at least~~ one ~~selected from the group consisting~~ of a sputtering method and an LPCVD method.

75. (Currently Amended) ~~A~~ The method according to claim 8,

wherein the amorphous semiconductor film is formed through a plasma CVD method at a temperature in a range of 400°C or higher.

76. (Currently Amended) ~~A~~ The method according to claim 8,

wherein the metal element comprises at least one selected from the group consisting of Fe, Co, Ni, Ru, Rh, Pd, Os, Ir, Pt, Cu, Ag, Au, Sn and Sb.

77. (Currently Amended) ~~A~~ The method according to claim 8,

wherein the semiconductor device is one selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle type display, a player using a recording medium, a digital camera, a front type projector, a rear type projector, a mobile telephone, a mobile book, and a display.

78. (previously presented) A method of manufacturing a semiconductor device, ~~said~~ the method comprising the steps of:

irradiating a semiconductor film with a laser light to improve crystallinity of the semiconductor film wherein a warp is created in the semiconductor film due to the ~~irradiation of~~ irradiating with the laser light;

heating the ~~crystallized~~ semiconductor film in order to decrease the warp; and

etching the ~~crystallized~~ semiconductor film to form at least one semiconductor island after ~~said~~ the heating step.

79. (Currently Amended) The method according to claim 78,

wherein the semiconductor film comprises amorphous silicon.

80. (Currently Amended) The method according to claim 78,

wherein ~~said~~ the semiconductor film is crystallized before the ~~irradiation~~ irradiating with the laser light.

81. (Currently Amended) The method according to claim 78,

wherein ~~said~~ the semiconductor film is crystallized before the irradiation with the laser light where the crystallization of the semiconductor film is promoted by adding a metal element thereto.

82. (New) A method of manufacturing a semiconductor device, the method comprising the steps of:

irradiating a semiconductor film with a laser light to improve crystallinity of the semiconductor film wherein a warp is created in the semiconductor film due to the irradiating with the laser light;

etching the semiconductor film to form at least one semiconductor island; and

heating the semiconductor film in order to decrease the warp after the etching step.

83. (New) The method according to claim 78,

wherein the semiconductor film comprises amorphous silicon.

84. (New) The method according to claim 78,

wherein the semiconductor film is crystallized before the irradiation with the laser light.

85. (New) The method according to claim 78,

wherein the semiconductor film is crystallized before the irradiation with the laser light where the crystallization of the semiconductor film is promoted by adding a metal element thereto.